LUXNET
CORPORATION

48400 Fremont Blvd.
Fremont, CA 94538 USA
Tel: (510) 445-3068 x 244
Fax: (510) 445-3060

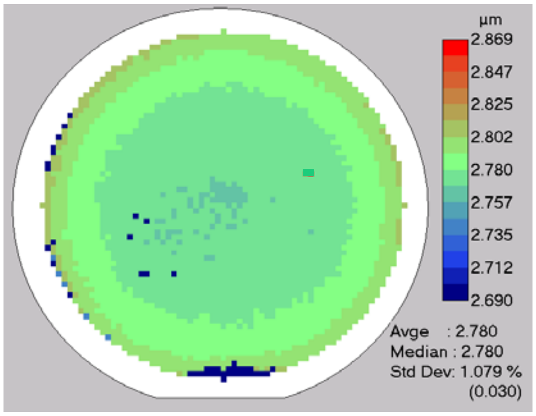
50, Lung-Yuan 7th Road, Lung-Tan
Tao-Yuan Hsien, TAIWAN
Tel: (03) 409-1335 x 230/235
Fax: (03) 409-1339

850nm PIN Epiwafer

Part Number: PG1A-1000

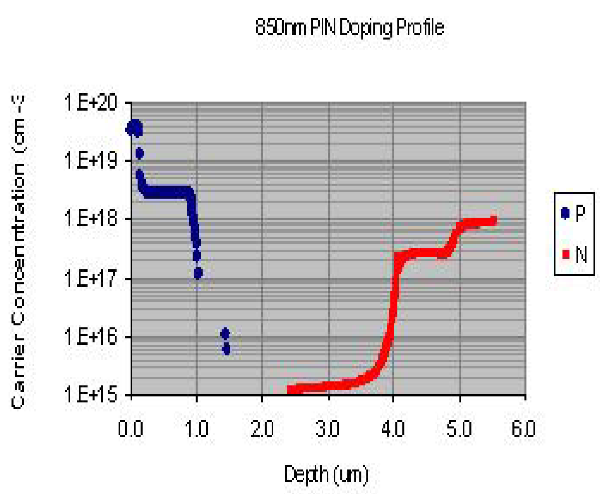
LuxNet’s 850nm PIN epi structure was produced using a state-of-the-art MOCVD reactor. We achieved excellent uniformity and reproducibility. Thickness uniformity is better than 1% within a 3” wafer.

Characterization



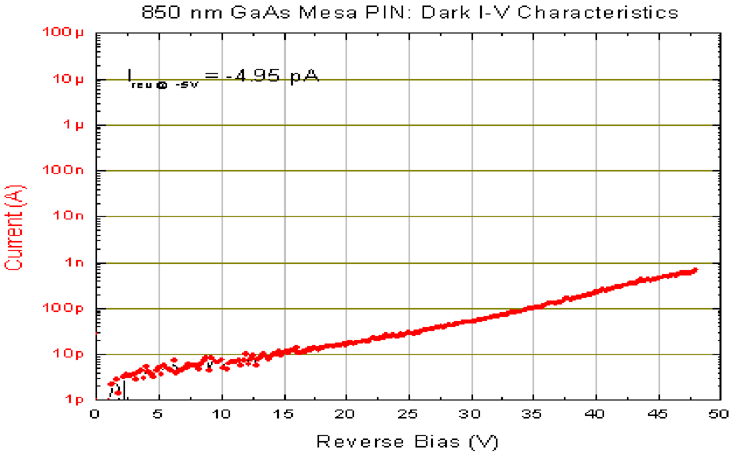
Features

- Excellent thickness uniformity



- GaAs absorption layer carrier
- Si & C dopant
- Custom structure available by request

Device Performance



- Dark Current @ 5V ~2 pA
- Breakdown Voltage > 50V